## NSN 5961-00-515-3296

**Fiig:** A110a0

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View Online at https://aerobasegroup.com/nsn/5961-00-515-3296 **Inclosure Material:** Metal **Overall Length:** Between 0.240 inches and 0.290 inches **Overall Height:** Between 0.030 inches and 0.080 inches Overall Width: Between 0.120 inches and 0.154 inches **Component Name And Quantity:** 2 transistor **Mounting Method:** Press fit **Features Provided:** Burn in and hermetically sealed case **Semiconductor Material:** Silicon all transistor **Voltage Rating In Volts Per Characteristic:** 40.0 collector to base voltage, dc all transistor and 40.0 collector to emitter voltage, dc all transistor and 5.0 emitter to base voltage, dc all transistor **Current Rating Per Characteristic:** 1.00 amperes source cutoff current all transistor **Power Rating Per Characteristic:** 350.0 milliwatts small-signal input power, common-collector absolute all transistor **Maximum Operating Tempurature Per Measurement Point:** 200.0 degrees celsius junction **Special Features:** All transistor junction pattern arrangement: pnp **Terminal Type And Quantity:** 6 ribbon Shelf Life: N/a **Unit Of Measure: Demilitarization:** No